

# Jiahuan

## List of Publications by Year in descending order

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17  
papers

572  
citations

687363

13  
h-index

839539

18  
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all docs

18  
docs citations

18  
times ranked

649  
citing authors

| #  | ARTICLE  | IF   | CITATIONS |
|----|--|------|-----------|
| 1  | Monolayer tellureneâ€metal contacts. Journal of Materials Chemistry C, 2018, 6, 6153-6163.   | 5.5  | 81        |
| 2  | Sub 10 nm Bilayer Bi <sub>2</sub> O <sub>2</sub> Se Transistors. Advanced Electronic Materials, 2019, 5, 1800720.  | 5.1  | 70        |
| 3  | Excellent Device Performance of Subâ€5â€nm Monolayer Tellurene Transistors. Advanced Electronic Materials, 2019, 5, 1900226.   | 5.1  | 65        |
| 4  | Gate-tunable interfacial properties of in-plane ML MX <sub>2</sub> 1Tâ€2â€H heterojunctions. Journal of Materials Chemistry C, 2018, 6, 5651-5661.                                       | 5.5  | 54        |
| 5  | Schottky Contact in Monolayer WS <sub>2</sub> Fieldâ€Effect Transistors. Advanced Theory and Simulations, 2019, 2, 1900001.  | 2.8  | 42        |
| 6  | Sub-5-nm Monolayer Silicane Transistor: A First-Principles Quantum Transport Simulation. Physical Review Applied, 2020, 14, .  | 3.8  | 38        |
| 7  | n-Type Ohmic contact and p-type Schottky contact of monolayer InSe transistors. Physical Chemistry Chemical Physics, 2018, 20, 24641-24651.  | 2.8  | 33        |
| 8  | Monolayer GaS with high ion mobility and capacity as a promising anode battery material. Journal of Materials Chemistry A, 2019, 7, 14042-14050.   | 10.3 | 32        |
| 9  | Reexamination of the Schottky Barrier Heights in Monolayer MoS <sub>2</sub> Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 4717-4726.                                    | 5.0  | 27        |
| 10 | Interfacial Properties of Monolayer Antimonene Devices. Physical Review Applied, 2019, 11, .   | 3.8  | 22        |
| 11 | Unusual Fermiâ€Level Pinning and Ohmic Contact at Monolayer Bi <sub>2</sub> O <sub>2</sub> Seâ€Metal Interface. Advanced Theory and Simulations, 2019, 2, 1800178.                       | 2.8  | 20        |
| 12 | Planar Directionâ€Dependent Interfacial Properties in Monolayer In <sub>2</sub> Se <sub>3</sub> â€Metal Contacts. Physica Status Solidi (B): Basic Research, 2020, 257, 1900198.         | 1.5  | 19        |
| 13 | Pervasive Ohmic Contacts in Bilayer Bi <sub>2</sub> O <sub>2</sub> Seâ€Metal Interfaces. Journal of Physical Chemistry C, 2019, 123, 8923-8931.  | 3.1  | 17        |
| 14 | n- and p-type ohmic contacts at monolayer gallium nitrideâ€metal interfaces. Physical Chemistry Chemical Physics, 2018, 20, 24239-24249.   | 2.8  | 13        |
| 15 | Computational Study of Ohmic Contact at Bilayer InSe-Metal Interfaces: Implications for Field-Effect Transistors. ACS Applied Nano Materials, 2019, 2, 6898-6908.                        | 5.0  | 13        |
| 16 | Bilayer tellureneâ€metal interfaces. Journal of Semiconductors, 2019, 40, 062003.  | 3.7  | 9         |
| 17 | First-principles simulation of monolayer hydrogen passivated Bi <sub>2</sub> O <sub>2</sub> S <sub>2</sub> â€metal interfaces. Physical Chemistry Chemical Physics, 2020, 22, 7853-7863. | 2.8  | 9         |